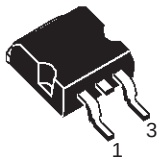
STB40NF10

N - CHANNEL 100V - 0.030Ω - 40A TO-263
LOW GATE CHARGE STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STB40NF10	100 V	< 0.035 Ω	40 A

- TYPICAL $R_{DS(on)}$ = 0.030 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- SURFACE-MOUNTING D2PAK (TO-263) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")



D^2PAK
TO-263
(Suffix "T4")

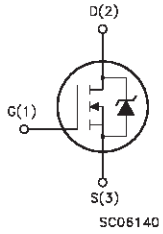
DESCRIPTION

This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	100	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	100	V
V_{GS}	Gate-source Voltage	± 20	V
I_D	Drain Current (continuous) at T_c = 25 °C	40	A
I_D	Drain Current (continuous) at T_c = 100 °C	25	A
I_{DM}(•)	Drain Current (pulsed)	160	A
P_{tot}	Total Dissipation at T_c = 25 °C	140	W
	Derating Factor	0.93	W/°C
E_{AS}(1)	Single Pulse Avalanche Energy	135	mJ
T_{stg}	Storage Temperature	-65 to 175	°C
T_j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area (1) starting T_j = 25 °C, I_D =40A , V_{DD} = 50V

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case Max	1.07	$^oC/W$
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient Max	62.5	$^oC/W$
T_l	Maximum Lead Temperature For Soldering Purpose	300	^oC

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	100			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0) V_{DS} = Max Rating V_{DS} = Max Rating T_c =125 ^oC				1 10	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	2	2.8	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 20 A		0.030	0.035	Ω
$I_{D(on)}$	On State Drain Current	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$ V_{GS} = 10 V	40			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$ I_D =20 A		20		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0		1800 270 110		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 50 V I_D = 20 A R_G = 4.7 Ω V_{GS} = 10 V (Resistive Load, see fig. 3)		28 63		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 80 V I_D = 40 A V_{GS} = 10 V		60 10 23	80	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 50 V I_D = 20 A R_G = 4.7 Ω V_{GS} = 10 V (Resistive Load, see fig. 3)		84 28		ns ns
$t_{d(off)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	Vclamp = 80 V I_D = 40 A R_G = 4.7 Ω V_{GS} = 10 V (Inductive Load, see fig. 5)		71 36 70		ns ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				40 160	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 40 A V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 40 A di/dt = 100 A/µs V_{DD} = 50 V T_j = 150 °C (see test circuit, fig. 5)		114 456 8		ns nC A

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

Fig. 1: Unclamped Inductive Load Test Circuit

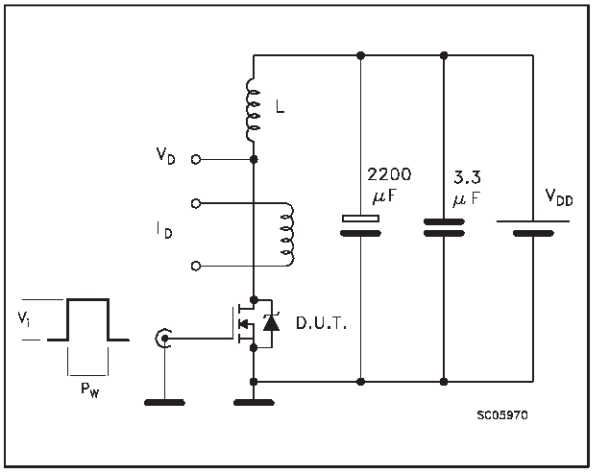


Fig. 2: Unclamped Inductive Waveform

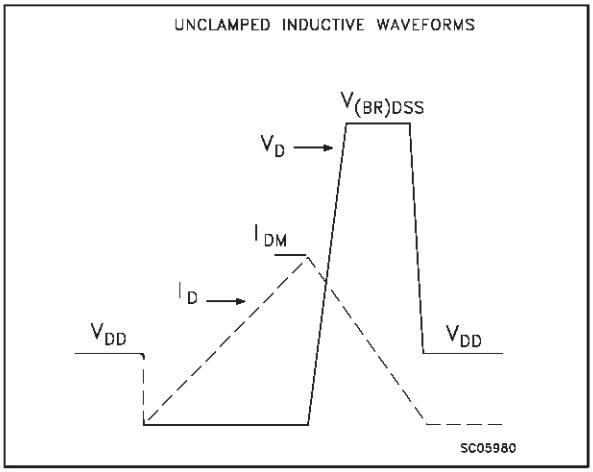


Fig. 3: Switching Times Test Circuits For Resistive Load

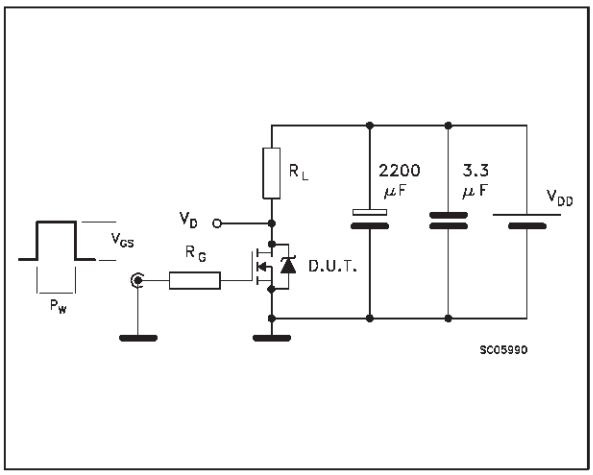


Fig. 4: Gate Charge test Circuit

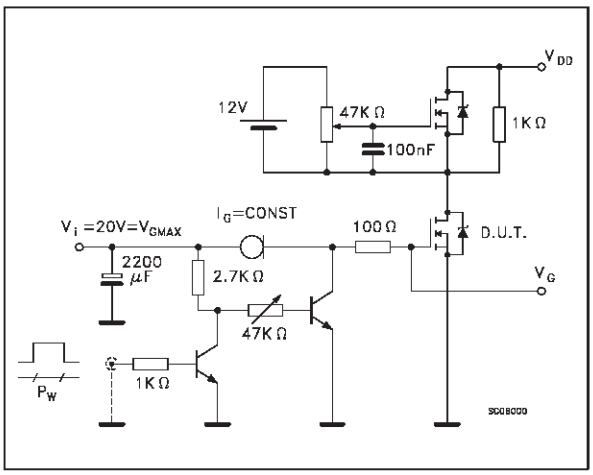
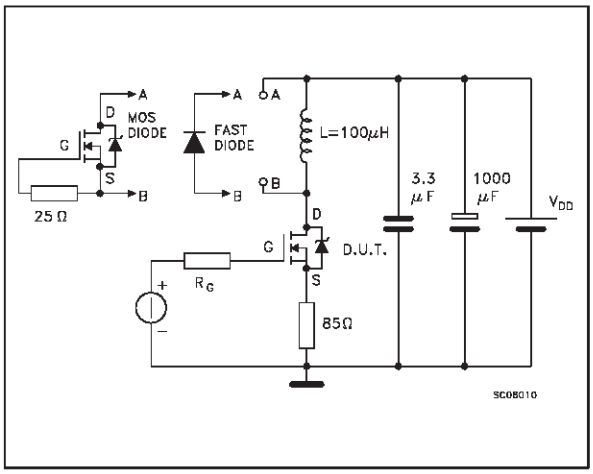
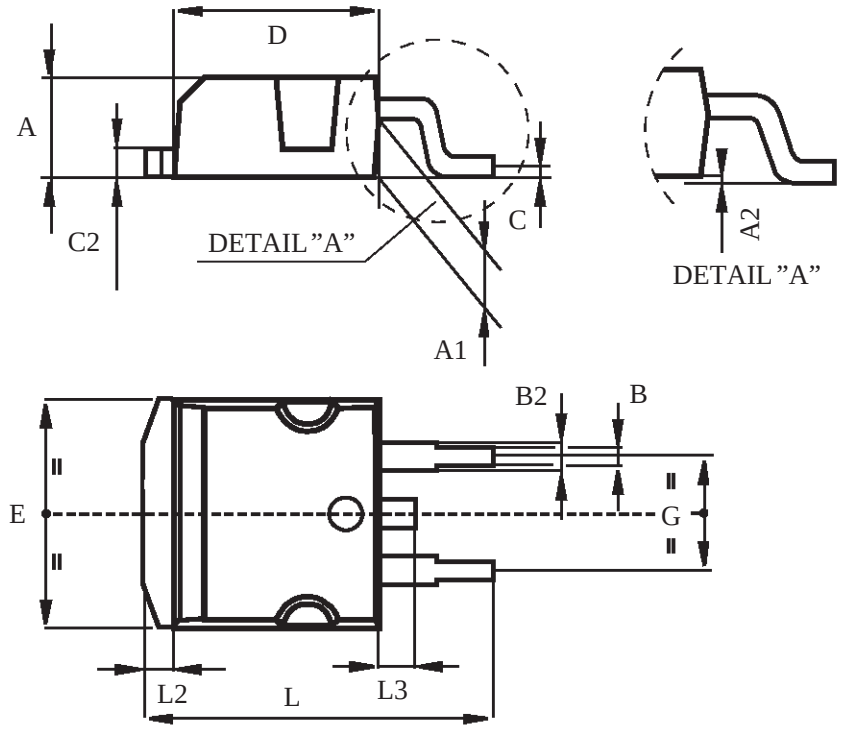


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-263 (D^2PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	8.95		9.35	0.352		0.368
E	10		10.4	0.393		0.409
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068



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